

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	16	"3-mask process"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/10 16:20
S2	9	S1 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:40
S3	1	10/814186	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/21 14:10
S4	0	2004/0129943	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/22 09:18
S5	1	("20040129943").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/02/22 09:18
S6	0	("2004/0129943").URPN.	USPAT	OR	ON	2006/02/22 09:18
S7	13	("5010027" "5346833" "5478766").PN. OR ("6274400").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/22 09:27
S8	59	("4778560" "4783147" "5008218" "5015597" "5032531" "5166085" "5166086" "5231039").PN. OR ("5478766").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/22 09:40
S9	19	("5346833" "5366912" "5478766" "5610082" "5621556" "5648674" "5717223" "5811325" "5962896" "6008065" "6184947" "6184960" "6242758" "6243146" "6274400").PN. OR ("6436740").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/22 09:42
S10	139	("3-mask process" or "three mask process")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/22 09:51

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S11	62	S10 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 12:27
S12	18	S11 and TFT	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:39
S13	17307	LCD and TFT	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/22 09:51
S14	36	S13 and ("3-mask process" or "three mask process")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/22 09:51
S15	15	S14 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 12:28
S16	48	LCD and ("3-mask process" or "three mask process")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:44
S17	15	S16 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 12:28
S18	1	10/814186	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 12:28
S19	40	tft and ("3-mask process" or "three mask process")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:22
S20	67825	TFT	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:39

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S21	45198	S20 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:40
S22	3859	S21 and ("3-mask process" or "source/drain region" or photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 08:31
S23	0	S21 and ("3-mask process") with ("source/drain region" near10 photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:43
S24	34	S21 and ("source/drain region" near10 photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:43
S25	0	S24 and ("3-mask process" or "three mask process")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:44
S26	18	S21 and ("3-mask process" or "three mask process")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/24 13:44
S27	67825	TFT	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 08:31
S28	45198	S27 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 08:31
S29	8	S28 and ("3-mask process")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 08:34
S30	3245	S28 and (photoresist or novolak)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:06

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S31	133	S30 and (reduce\$ with remove\$)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 10:55
S32	14	S30 and "active" same (reduce\$ with remove\$)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 10:47
S33	14	S31 and "source/drain region"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 10:55
S34	10249	((438/30,151,745,149) or (257/59,72) or (349/139,108,43)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/02/27 12:29
S35	179128	(lcd or "liquid crystal display device")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 12:30
S36	5137	S34 and (lcd or "liquid crystal display device")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 12:30
S37	4077	S36 and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 12:30
S38	1053	S37 and "gate electrode" same "active layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 12:31
S39	78	S38 and (remove\$ same "active layer" same ((source or drain) adj region))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 12:32
S40	40	S39 and (photoresist or novolak)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 12:51

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S41	106	S34 and (("3-mask" or "third mask") near process)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/02/27 12:53
S42	10	(("5920362") or ("6413804") or ("6614083") or ("20030058392") or ("20030128309") or ("20030162338") or ("5550071") or ("20040233361") or ("20040043545") or ("20040041956")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/03/10 16:21
S43	10402	((438/30,151,745,149) or (257/59,72) or (349/139,108,43)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2006/03/28 12:48
S44	4230	S43 and ((active or (amorphous adj silicon) or (a-Si) or (a:Si)) adj (layer or region))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 12:50
S45	3924	S44 and (remov\$4 or etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 12:48
S46	3780	S45 and ((source/drain) or source or drain or S/D or LDD)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 12:49
S47	451	S43 and (((active or (amorphous adj silicon) or (a-Si) or (a:Si)) adj (layer or region)) near10 (remov\$4 or etch\$3) near10 ((source/drain) or source or drain or S/D or LDD))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 13:41
S48	360	S47 and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 12:51
S49	176	S48 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 13:38

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S50	216	S47 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:06
S51	1503	((active or (amorphous adj silicon) or (a-Si) or (a:Si)) adj (layer or region)) near10 (remov\$4 or etch\$3) near10 ((source/drain) or source or drain or S/D or LDD))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 13:41
S52	661	S51 and (photoresist or novolak)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:06
S53	347	S52 and @pd<"20030402"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:06
S54	11	S53 and (lift-off adj process)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:44
S55	7	S43 and (conductive same photoresist same (lift-off adj process))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:52
S56	0	S49 and (conductive same photoresist same (lift-off adj process))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:52
S57	0	S50 and (conductive same photoresist same (lift-off adj process))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:52
S58	5227	S43 and (lcd or "liquid crystal display device")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:52
S59	7	S58 and (conductive same photoresist same (lift-off adj process))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 14:58

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S60	11	S58 and (lift-off same etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 15:34
S61	34	S43 and (lift-off same etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/28 15:34